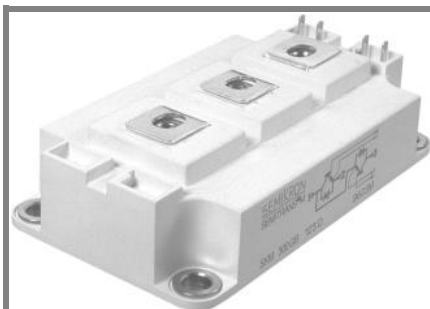




SEMITRANS® 3

Trench IGBT Modules

SKM 300GB066D

Preliminary Data

Features

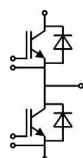
- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability, self limiting to $6 \times I_C$

Typical Applications

- AC inverter drives
- UPS
- Electronic welders

Remarks

- Case temperature limited to $T_C = 125^\circ\text{C}$ max, recommended $T_{op} = -40 \dots +150^\circ\text{C}$
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- Take care of over-voltage caused by stray inductances

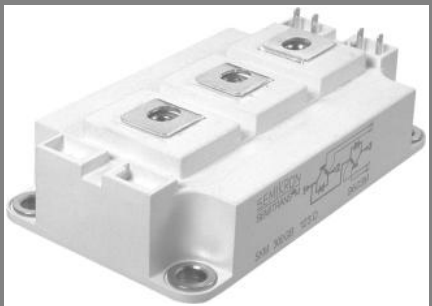


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Absolute Maximum Ratings		T _{case} = 25°C, unless otherwise specified		
Symbol	Conditions		Values	Units
IGBT				
V _{CES}	T _j = 25 °C		600	V
I _C	T _j = 175 °C	T _c = 25 °C	390	A
		T _c = 80 °C	300	A
I _{CRM}	I _{CRM} =2xI _{Cnom}		600	A
V _{GES}			± 20	V
t _{psc}	V _{CC} = 360 V; V _{GE} ≤ 15 V; T _j = 150 °C V _{CES} < 600 V		6	μs
Inverse Diode				
I _F	T _j = 175 °C	T _c = 25 °C	350	A
		T _c = 80 °C	250	A
I _{FRM}	I _{FRM} =2xI _{Fnom}		600	A
I _{FSM}	t _p = 10 ms; sin.	T _j = 175 °C	1760	A
Module				
I _{t(RMS)}			500	A
T _{vj}			- 40 ... + 175	°C
T _{stg}			- 40 ... + 125	°C
V _{isol}	AC, 1 min.		4000	V

Characteristics			T _{case} = 25°C, unless otherwise specified			
Symbol	Conditions		min.	typ.	max.	Units
IGBT						
V _{GE(th)}	V _{GE} = V _{CE} , I _C = 4,8 mA		5	5,8	6,5	V
I _{CES}	V _{GE} = 0 V, V _{CE} = V _{CES}	T _j = 25 °C		0,15	0,45	mA
V _{CE0}		T _j = 25 °C		0,9	1	V
		T _j = 150 °C		0,85	0,9	V
r _{CE}	V _{GE} = 15 V	T _j = 25°C		1,8	3	mΩ
		T _j = 150°C		2,7	3,8	mΩ
V _{CE(sat)}	I _{Cnom} = 300 A, V _{GE} = 15 V	T _j = 25°C _{chiplev.}		1,45	1,9	V
		T _j = 150°C _{chiplev.}		1,7	2,1	V
C _{ies}	V _{CE} = 25, V _{GE} = 0 V	f = 1 MHz		18,5		nF
C _{oes}				1,2		nF
C _{res}				0,55		nF
Q _G	V _{GE} = -8V...+15V			2400		nC
R _{Gint}	T _j = °C			1		Ω
t _{d(on)}	R _{Gon} = 2,4 Ω	V _{CC} = 300V I _{Cnom} = 300A T _j = 150 °C V _{GE} = -8V/+15V		150		ns
t _r				48		ns
E _{on}				7,5		mJ
t _{d(off)}	R _{Goff} = 2,4 Ω			540		ns
t _f				53		ns
E _{off}			11,5		mJ	
R _{th(j-c)}	per IGBT				0,15	K/W

SKM 300GB066D



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Preliminary Data

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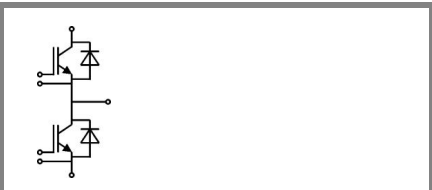
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Characteristics					
Symbol	Conditions	min.	typ.	max.	Units
Inverse Diode					
$V_F = V_{EC}$	$I_{Fnom} = 300\text{ A}$; $V_{GE} = 0\text{ V}$ $T_j = 25^\circ\text{C}_{chiplev.}$		1,4	1,6	V
V_{F0}	$T_j = 25^\circ\text{C}$		0,95	1	V
r_F	$T_j = 25^\circ\text{C}$		1,5	2	mΩ
I_{RRM}	$I_{Fnom} = 300\text{ A}$ $T_j = 150^\circ\text{C}$		340		A
Q_{rr}	$di/dt = 7000\text{ A}/\mu\text{s}$		47		μC
E_{rr}	$V_{GE} = -8\text{ V}$; $V_{CC} = 300\text{ V}$		10,5		mJ
$R_{th(j-c)D}$	per diode			0,25	K/W
Module					
L_{CE}			15	20	nH
$R_{CC'+EE'}$	res., terminal-chip $T_{case} = 25^\circ\text{C}$		0,35		mΩ
	$T_{case} = 125^\circ\text{C}$		0,5		mΩ
$R_{th(c-s)}$	per module			0,038	K/W
M_s	to heat sink M6	3		5	Nm
M_t	to terminals M6	2,5		5	Nm
w				325	g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.

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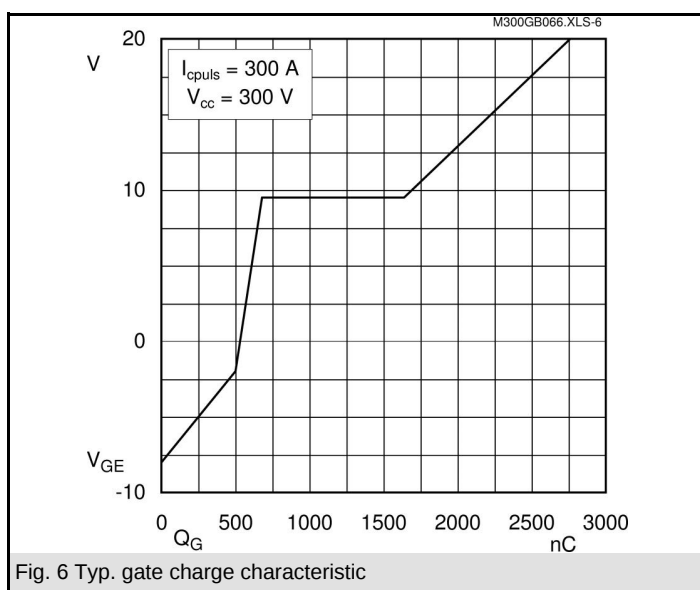
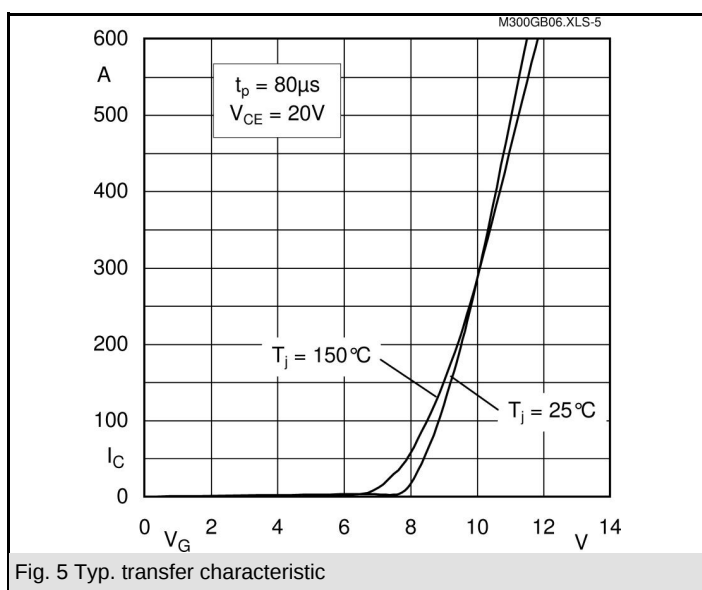
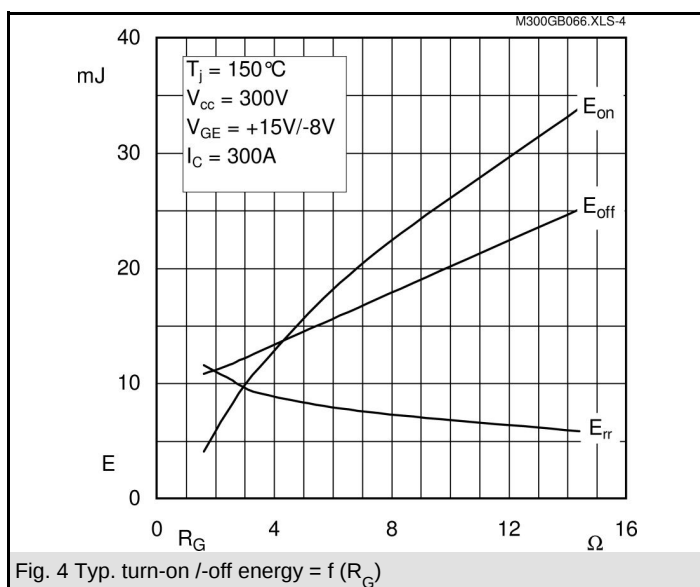
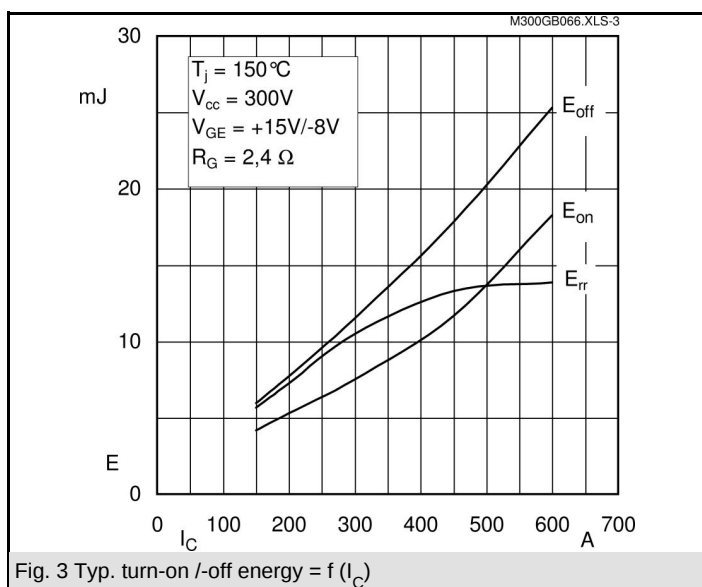
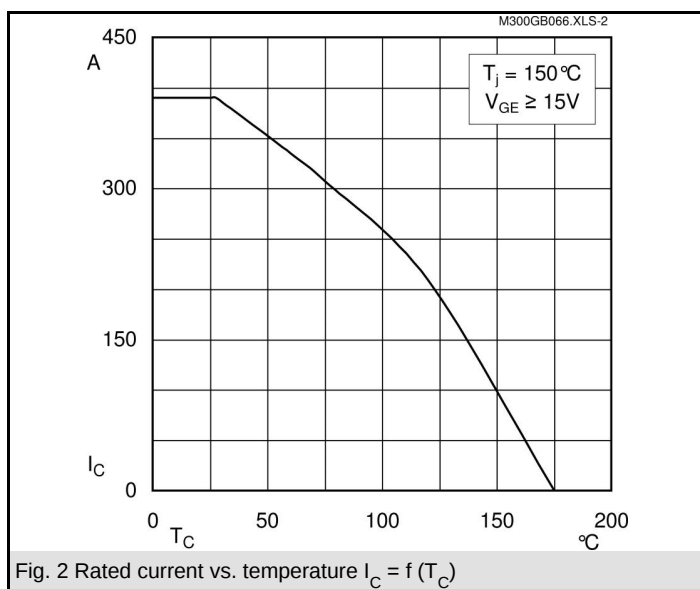
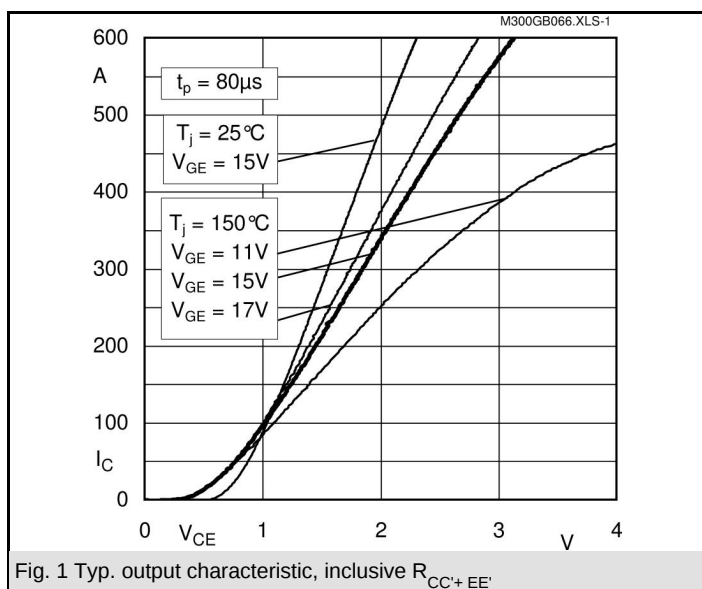
Remarks

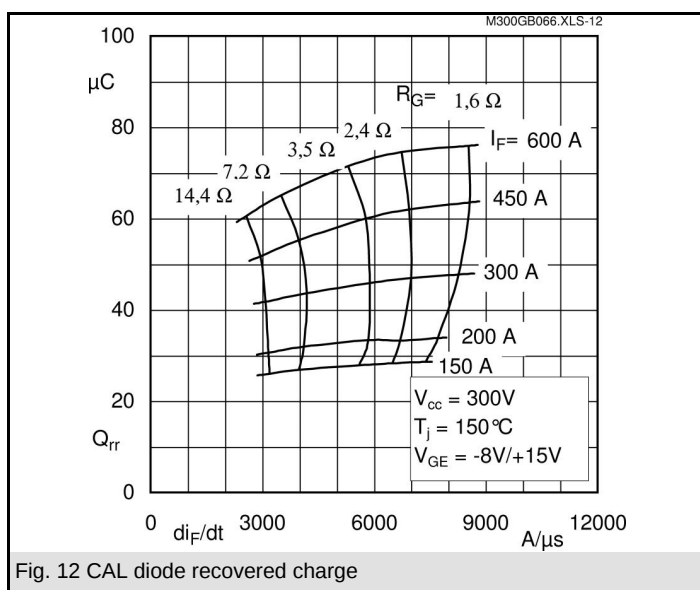
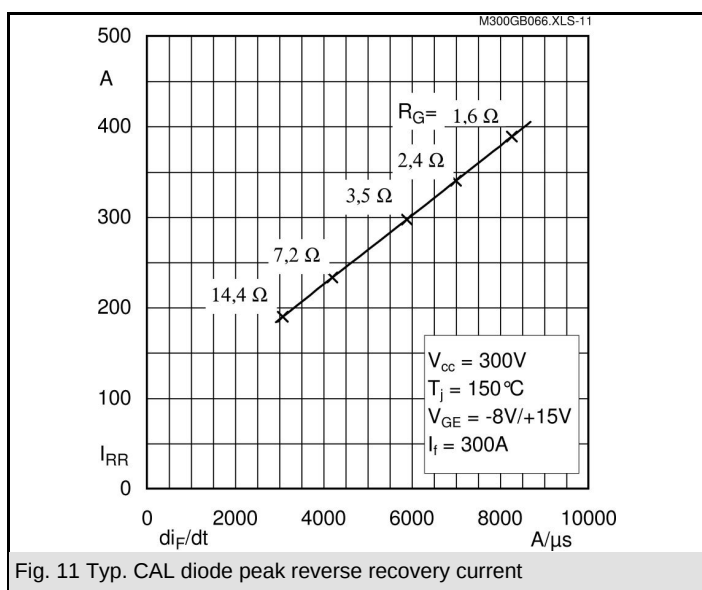
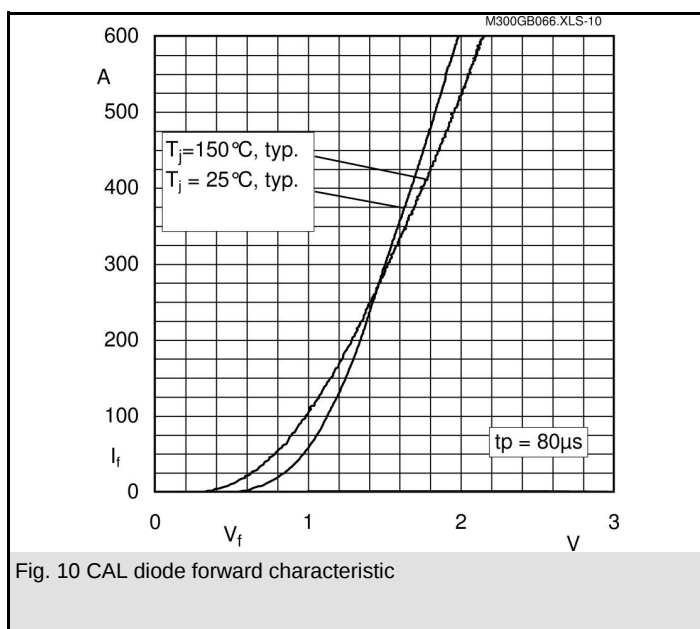
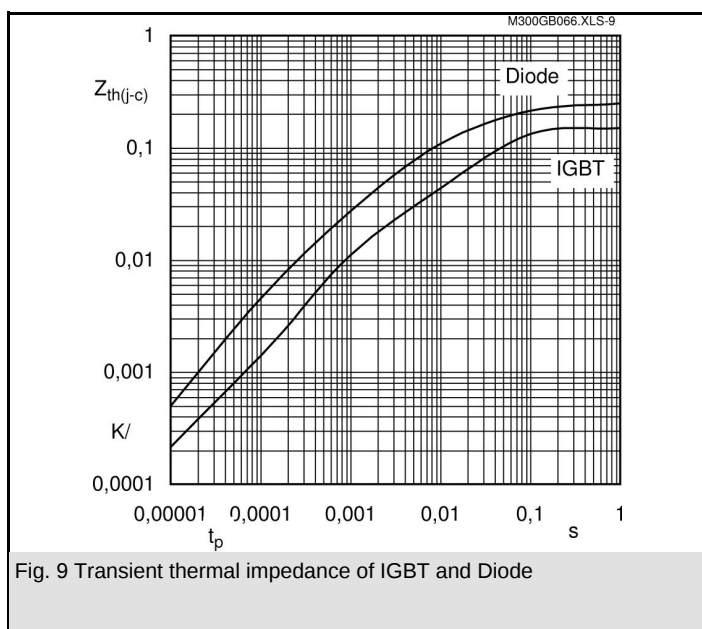
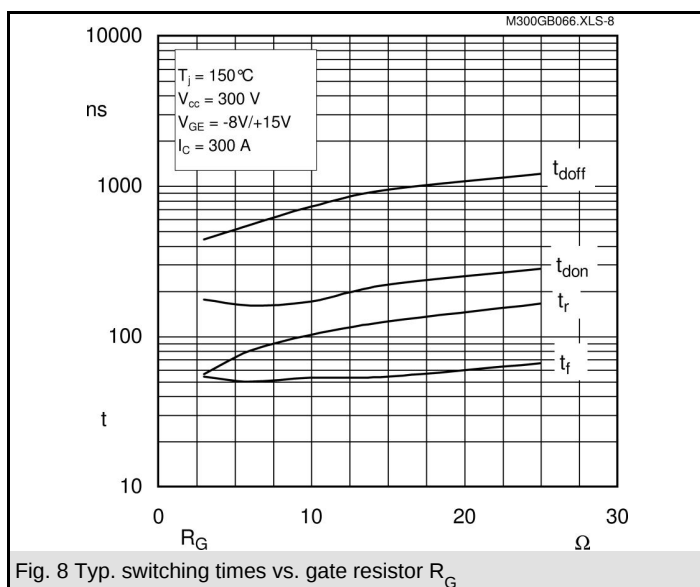
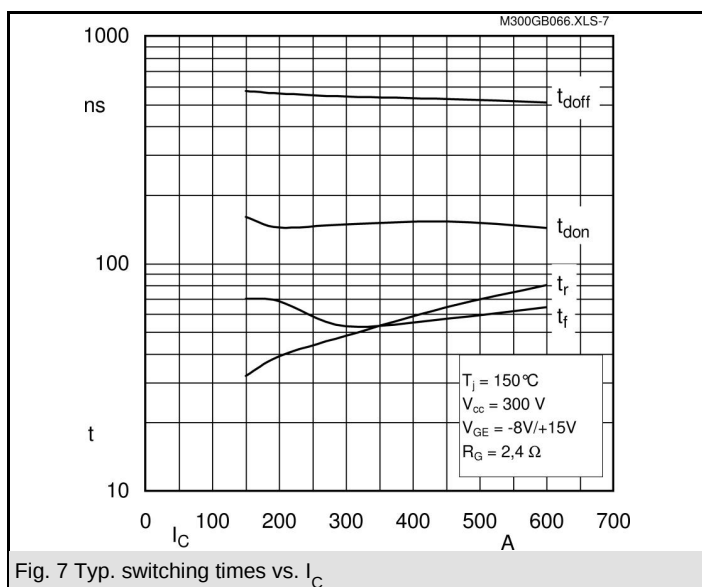
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Z_{th}			
Symbol	Conditions	Values	Units
$Z_{th(j-c)I}$			
R_i	$i = 1$	107	mk/W
R_i	$i = 2$	30	mk/W
R_i	$i = 3$	11,6	mk/W
R_i	$i = 4$	1,4	mk/W
τ_{u_i}	$i = 1$	0,054	s
τ_{u_i}	$i = 2$	0,0144	s
τ_{u_i}	$i = 3$	0,0007	s
τ_{u_i}	$i = 4$	0,0004	s
$Z_{th(j-c)D}$			
R_i	$i = 1$	140	mk/W
R_i	$i = 2$	82	mk/W
R_i	$i = 3$	23,5	mk/W
R_i	$i = 4$	4,5	mk/W
τ_{u_i}	$i = 1$	0,054	s
τ_{u_i}	$i = 2$	0,01	s
τ_{u_i}	$i = 3$	0,0015	s
τ_{u_i}	$i = 4$	0,0002	s

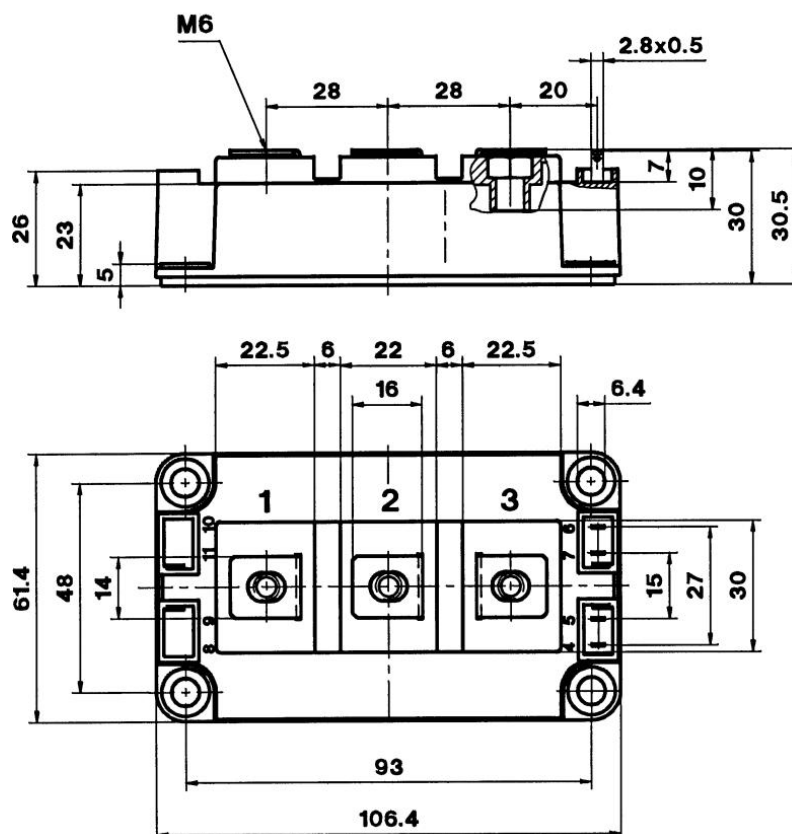


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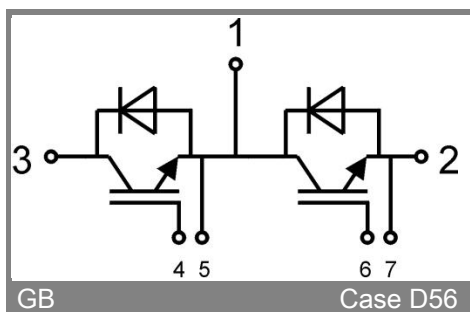




CASED56



Case D 56



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Case D56